

Thierry Baron

List of Publications by Year in descending order

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243
papers

5,076
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76326

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248
times ranked

5168
citing authors

#	ARTICLE	IF	CITATIONS
1	Single-Mode Photonic Crystal Nanobeam Lasers Monolithically Grown on Si for Dense Integration. IEEE Journal of Selected Topics in Quantum Electronics, 2022, 28, 1-6.	2.9	4
2	Large-Scale Monolithic Fabrication of III-V Vertical Nanowires on a Standard Si(100) Microelectronic Substrate. ACS Omega, 2022, 7, 5836-5843.	3.5	4
3	Impact of Substrate Biasing During AlN Growth by PEALD on Al ₂ O ₃ /AlN/GaN MOS Capacitors. Advanced Materials Interfaces, 2022, 9, 2101731.	3.7	2
4	200 mm-scale growth of 2D layered GaSe with preferential orientation. APL Materials, 2022, 10, 051106.	5.1	1
5	Selective epitaxial growth of AlGaAs/GaAs heterostructures on 300Åmm Si(001) for red optical emission. Thin Solid Films, 2021, 721, 138541.	1.8	5
6	3D field confinement in the near-field interaction between graphene and Si/SiGe axially heterostructured NWs. Applied Physics Letters, 2021, 118, 211104.	3.3	0
7	Gallium Selenide Nanoribbons on Silicon Substrates for Photodetection. ACS Applied Nano Materials, 2021, 4, 7820-7831.	5.0	5
8	Monolithically integrated InGaAs/AlGaAs multiple quantum well photodetectors on 300Åmm Si wafers. AIP Advances, 2021, 11, .	1.3	5
9	Origin of Defect Tolerance in InAs/GaAs Quantum Dot Lasers Grown on Silicon. Journal of Lightwave Technology, 2020, 38, 240-248.	4.6	46
10	A fabrication process for self-connected horizontal SiGe nanowires. Microelectronic Engineering, 2020, 220, 111150.	2.4	1
11	Kinetic study of hydrogen lateral diffusion at high temperature in a directly-bonded InP-SiO ₂ /Si substrate. Nanotechnology, 2020, 31, 135205.	2.6	1
12	Epitaxial Growth of High-Quality AlGaInAs-Based Active Structures on a Directly Bonded InP-SiO ₂ /Si Substrate. Physica Status Solidi (A) Applications and Materials Science, 2020, 217, 1900523.	1.8	8
13	Study of physisorption phenomena of chemical species on 300Åmm Si wafers during controlled mini-environment transfers between microelectronic equipments. Microelectronic Engineering, 2020, 231, 111401.	2.4	3
14	Monolithic integration of GaAs p-i-n photodetectors grown on 300 mm silicon wafers. AIP Advances, 2020, 10, .	1.3	5
15	Improvement of AlN Film Quality Using Plasma Enhanced Atomic Layer Deposition with Substrate Biasing. ACS Applied Materials & Interfaces, 2020, 12, 39870-39880.	8.0	20
16	O-Band Emitting InAs Quantum Dots Grown by MOCVD on a 300 mm Ge-Buffered Si (001) Substrate. Nanomaterials, 2020, 10, 2450.	4.1	5
17	Reversible Al Propagation in Si _x Ge _{1-x} Nanowires: Implications for Electrical Contact Formation. ACS Applied Nano Materials, 2020, 3, 10427-10436.	5.0	4
18	Comparison of AlGaInAs-Based Laser Behavior Grown on Hybrid InP-SiO ₂ /Si and InP Substrates. IEEE Photonics Technology Letters, 2020, 32, 469-472.	2.5	8

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19	Continuous-wave quantum dot photonic crystal lasers grown on on-axis Si (001). Nature Communications, 2020, 11, 977.	12.8	61
20	Etched-cavity GaSb laser diodes on a MOVPE GaSb-on-Si template. Optics Express, 2020, 28, 20785.	3.4	9
21	Fabry Perot Laser Arrays Covering C+L Band Obtained by Selective Area Growth on InP-SiO ₂ /Si Substrate. , 2020, , .		0
22	High-quality Epitaxial Growth of AlGaInAs-based Active Structure on a Directly-Bonded InPoSi Substrate. , 2019, , .		1
23	InAs/GaSb thin layers directly grown on nominal (0°0°1)-Si substrate by MOVPE for the fabrication of InAs FINFET. Journal of Crystal Growth, 2019, 510, 18-22.	1.5	3
24	O-band InAs/GaAs quantum dot laser monolithically integrated on exact (0°0°1) Si substrate. Journal of Crystal Growth, 2019, 511, 56-60.	1.5	31
25	Midwave infrared barrier detector based on Ga-free InAs/InAsSb type-II superlattice grown by molecular beam epitaxy on Si substrate. Infrared Physics and Technology, 2019, 96, 39-43.	2.9	29
26	Ultra-low threshold InAs/GaAs quantum dot microdisk lasers on planar on-axis Si (001) substrates. Optica, 2019, 6, 430.	9.3	37
27	Suppression of self-organized surface nanopatterning on GaSb/InAs multilayers induced by low energy oxygen ion bombardment by using simultaneously sample rotation and oxygen flooding. Applied Surface Science, 2018, 441, 218-222.	6.1	6
28	Indium-oxide nanoparticles for RRAM devices compatible with CMOS back-end-off-line. Solid-State Electronics, 2018, 143, 20-26.	1.4	6
29	Electrical properties of metal/Al ₂ O ₃ /In _{0.53} Ga _{0.47} As capacitors grown on InP. Journal of Applied Physics, 2018, 123, 161534.	2.5	8
30	Massless Dirac Fermions in ZrTe ₂ Semimetal Grown on InAs(111) by van der Waals Epitaxy. ACS Nano, 2018, 12, 1696-1703.	14.6	82
31	Electromagnetic field enhancement effects in group IV semiconductor nanowires. A Raman spectroscopy approach. Journal of Applied Physics, 2018, 123, .	2.5	6
32	Anti phase boundary free GaSb layer grown on 300 mm (001)-Si substrate by metal organic chemical vapor deposition. Thin Solid Films, 2018, 645, 5-9.	1.8	18
33	Low temperature growth and physical properties of InAs thin films grown on Si, GaAs and In _{0.53} Ga _{0.47} As template. Thin Solid Films, 2018, 645, 119-123.	1.8	6
34	Growth of Ge _{1-x} Sn _x Nanowires by Chemical Vapor Deposition via Vaporâ€“Liquidâ€“Solid Mechanism Using GeH ₄ and SnCl ₄ . Physica Status Solidi (A) Applications and Materials Science, 2018, 215, 1700743.	1.8	18
35	Direct measurement of AC electrokinetics properties and capture frequencies of silicon and siliconâ€“germanium nanowires. Semiconductor Science and Technology, 2018, 33, 015005.	2.0	1
36	Indium Oxide Nanostructure Optimization for RRAM Integration on CMOS BEOL. , 2018, , .		1

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37	Fano-resonances in High Index Dielectric Nanowires for Directional Scattering. Springer Series in Optical Sciences, 2018, , 283-309.	0.7	4
38	Direct examination of Si atoms spatial distribution and clustering in GaAs thin films with atom probe tomography. Scripta Materialia, 2018, 153, 109-113.	5.2	3
39	Understanding and improving the low optical emission of InGaAs quantum wells grown on oxidized patterned (001) silicon substrate. Applied Physics Letters, 2018, 112, .	3.3	2
40	Electromagnetic Field Enhancement on Axially Heterostructured NWs: The Role of the Heterojunctions. Journal of Electronic Materials, 2018, 47, 5072-5076.	2.2	1
41	Comprehension of peculiar local emission behavior of InGaAs quantum well by colocalized nanocharacterization combining cathodoluminescence and electron microscopy techniques. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2018, 36, 042901.	1.2	1
42	Growth dynamics of SiGe nanowires by the vapour-liquid-solid method and its impact on SiGe/Si axial heterojunction abruptness. Nanotechnology, 2018, 29, 355602.	2.6	6
43	Depth profiling investigation by pARXPS and MEIS of advanced transistor technology gate stack. Microelectronic Engineering, 2017, 169, 24-28.	2.4	9
44	Benefits of XPS nanocharacterization for process development and industrial control of thin SiGe channel layers in advanced CMOS technologies. Materials Science in Semiconductor Processing, 2017, 70, 105-110.	4.0	6
45	Fabrication of top-down gold nanostructures using a damascene process. Microelectronic Engineering, 2017, 177, 41-45.	2.4	6
46	Monolithically Integrated Electrically Pumped Continuous-Wave III-V Quantum Dot Light Sources on Silicon. IEEE Journal of Selected Topics in Quantum Electronics, 2017, 23, 1-10.	2.9	28
47	Fabrication of monodisperse magnetic nanoparticles released in solution using a block copolymer template. Journal Physics D: Applied Physics, 2017, 50, 295001.	2.8	3
48	Sub-10nm plasma nanopatterning of InGaAs with nearly vertical and smooth sidewalls for advanced n-fin field effect transistors on silicon. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2017, 35, 021206.	1.2	2
49	Fabrication and characterization of a germanium nanowire light emitting diode. Applied Physics Letters, 2017, 111, 233103.	3.3	2
50	Indium-oxide nanoparticles for Ox-RRAM in CMOS back-end-off-line. , 2017, , .		1
51	Strongly Directional Scattering from Dielectric Nanowires. ACS Photonics, 2017, 4, 2036-2046.	6.6	67
52	Electrically pumped continuous-wave 13 μm InAs/GaAs quantum dot lasers monolithically grown on on-axis Si (001) substrates. Optics Express, 2017, 25, 4632.	3.4	102
53	InGaAs-OI Substrate Fabrication on a 300 mm Wafer. Journal of Low Power Electronics and Applications, 2016, 6, 19.	2.0	3
54	300 mm InGaAs-on-insulator substrates fabricated using direct wafer bonding and the Smart Cut™ technology. Japanese Journal of Applied Physics, 2016, 55, 04EB10.	1.5	18

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55	Electroluminescence from NiSi ₂ /Si/NiSi ₂ nanowire heterostructures operated at high electric fields. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2016, 213, 2895-2900.	1.8	1
56	pH driven addressing of silicon nanowires onto Si ₃ N ₄ /SiO ₂ micro-patterned surfaces. <i>Nanotechnology</i> , 2016, 27, 295602.	2.6	42
57	Toward the III ^V /Si co-integration by controlling the biatomic steps on hydrogenated Si(001). <i>Applied Physics Letters</i> , 2016, 109, .	3.3	46
58	Enhanced nonlinear optical properties from individual silicon nanowires. , 2016, , .		0
59	Fabrication of GaAs nanowires and GaAs-Si axial heterostructure nanowires on Si (100) substrate for new applications. , 2016, , .		1
60	SIMS depth profiling and topography studies of repetitive III ^V trenches under low energy oxygen ion beam sputtering. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2016, 34, 03H131.	1.2	0
61	Spatially correlated structural and optical characterization of a single InGaAs quantum well fin selectively grown on Si by microscopy and cathodoluminescence techniques. <i>APL Materials</i> , 2016, 4, .	5.1	6
62	Epitaxial growth of antiphase boundary free GaAs layer on 300 mm Si(001) substrate by metalorganic chemical vapour deposition with high mobility. <i>APL Materials</i> , 2016, 4, .	5.1	99
63	3D Auger quantitative depth profiling of individual nanoscaled III ^V heterostructures. <i>Journal of Electron Spectroscopy and Related Phenomena</i> , 2016, 213, 1-10.	1.7	4
64	Threading dislocations in GaAs epitaxial layers on various thickness Ge buffers on 300 mm Si substrates. <i>Journal of Crystal Growth</i> , 2016, 453, 180-187.	1.5	24
65	Toward a Reliable Chipless RFID Humidity Sensor Tag Based on Silicon Nanowires. <i>IEEE Transactions on Microwave Theory and Techniques</i> , 2016, 64, 2977-2985.	4.6	73
66	Origin of second-harmonic generation from individual silicon nanowires. <i>Physical Review B</i> , 2016, 93, .	3.2	29
67	Depth profiling analysis of HfON on SiON ultrathin films by parallel angle resolved x ^{ray} photoelectron spectroscopy and medium energy ion scattering. <i>Surface and Interface Analysis</i> , 2016, 48, 436-439.	1.8	1
68	Fabrication and electrical characterization of homo- and hetero-structure Si/SiGe nanowire Tunnel Field Effect Transistor grown by vapor ^{liquid} solid mechanism. <i>Solid-State Electronics</i> , 2016, 118, 26-29.	1.4	17
69	Enhanced nonlinear optical response from individual silicon nanowires. <i>Physical Review B</i> , 2015, 91, .	3.2	23
70	Publisher's Note: Enhanced nonlinear optical response from individual silicon nanowires [<i>Phys. Rev. B</i> 91, 121416(R) (2015)]. <i>Physical Review B</i> , 2015, 91, .	3.2	0
71	Anti-phase boundaries ^{Free} GaAs epilayers on ^{quasi-nominal} Ge-buffered silicon substrates. <i>Applied Physics Letters</i> , 2015, 107, .	3.3	23
72	Chemical depth profiling and 3D reconstruction of III ^V heterostructures selectively grown on non ^{planar} Si substrates by MOCVD. <i>Physica Status Solidi - Rapid Research Letters</i> , 2015, 9, 202-205.	2.4	4

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73	Solar cells with gallium phosphide/silicon heterojunction. AIP Conference Proceedings, 2015, , .	0.4	8
74	Low Temperature Processing to Form Oxidation Insensitive Electrical Contact at Silicon Nanowire/Nanowire Junctions. Advanced Electronic Materials, 2015, 1, 1500172.	5.1	20
75	Silicon Nanowires: Low Temperature Processing to Form Oxidation Insensitive Electrical Contact at Silicon Nanowire/Nanowire Junctions (Adv. Electron. Mater. 10/2015). Advanced Electronic Materials, 2015, 1, .	5.1	0
76	Synthesis of mono disperse magnetic nanoparticles prepared on block copolymer templates for medical imaging techniques. , 2015, , .		0
77	300 mm InGaAsOI substrate fabrication using the Smart Cut TM technology. , 2015, , .		2
78	Evolution of Bulk c-Si Properties during the Processing of GaP/c-Si Heterojunction Cell. Energy Procedia, 2015, 77, 493-499.	1.8	36
79	Silicon nanonets for biological sensing applications with enhanced optical detection ability. Biosensors and Bioelectronics, 2015, 68, 336-342.	10.1	22
80	Percolating silicon nanowire networks with highly reproducible electrical properties. Nanotechnology, 2015, 26, 015201.	2.6	26
81	Nanoscale elemental quantification in heterostructured SiGe nanowires. Nanoscale, 2015, 7, 8544-8553.	5.6	7
82	Carbon Nanotube Sheet as Top Contact Electrode for Nanowires: Highly Versatile and Simple Process. Journal of Nanoscience and Nanotechnology, 2015, 15, 1669-1673.	0.9	4
83	Fabrication and characterization of silicon nanowire p-i-n MOS gated diode for use as p-type tunnel FET. Applied Physics A: Materials Science and Processing, 2015, 121, 1285-1290.	2.3	13
84	Al ₂ O ₃ /InGaAs interface study on MOS capacitors for a 300mm process integration. , 2015, , .		0
85	Functionalized silicon nanowires/conjugated polymer hybrid solar cells: Optical, electrical and morphological characterizations. Journal of Luminescence, 2015, 168, 315-324.	3.1	14
86	HfO ₂ /Al ₂ O ₃ /InGaAs MOSCAP Structures and InGaAs Plasma Nitridation Elaborated in a 300mm Pilot Line. ECS Transactions, 2015, 69, 9-13.	0.5	4
87	Chemical characterization of III-V heterostructures in 3D architecture. Microelectronic Engineering, 2015, 147, 219-222.	2.4	3
88	Low defect InGaAs quantum well selectively grown by metal organic chemical vapor deposition on Si(100) 300mm wafers for next generation non planar devices. Applied Physics Letters, 2014, 104, .	3.3	42
89	Dopant profiling in silicon nanowires measured by scanning capacitance microscopy. Physica Status Solidi - Rapid Research Letters, 2014, 8, 312-316.	2.4	11
90	Multimode Silicon Nanowire Transistors. Nano Letters, 2014, 14, 6699-6703.	9.1	31

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91	High density and taper-free boron doped Si _{1-x} Ge _x nanowire via two-step growth process. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2014, 32, 041401.	2.1	1
92	Growth strategies to control tapering in Ge nanowires. APL Materials, 2014, 2, .	5.1	16
93	Interfacial abruptness in axial Si/SiGe heterostructures in nanowires probed by scanning capacitance microscopy. Physica Status Solidi (A) Applications and Materials Science, 2014, 211, 509-513.	1.8	6
94	Control of heterointerface and strain mapping in Au catalyzed axial Si-Si _{1-x} Ge _x nanowires. Materials Research Society Symposia Proceedings, 2014, 1707, 37.	0.1	0
95	Strain mapping at the nanoscale using precession electron diffraction in transmission electron microscope with off axis camera. Applied Physics Letters, 2014, 105, 191906.	3.3	33
96	(Invited) SOI-Type Bonded Structures for Advanced Technology Nodes. ECS Transactions, 2014, 64, 35-48.	0.5	26
97	Impact of n -type doping on the carrier dynamics of silicon nanowires studied using optical-pump terahertz-probe spectroscopy. Physical Review B, 2014, 89, .	3.2	14
98	Control of the interfacial abruptness of Au-catalyzed Si-Si _{1-x} Ge _x heterostructured nanowires grown by vapor-liquid-solid. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2014, 32, .	2.1	4
99	(Invited) Photoluminescence Enhancement of a Silicon Nanocrystal Plane Positioned in the Near-Field of a Silicon Nanowire. ECS Transactions, 2014, 61, 189-197.	0.5	0
100	Composition-Dependent Interfacial Abruptness in Au-Catalyzed Si _{1-x} Ge _x /Si/Si _{1-x} Ge _x Nanowire Heterostructures. Nano Letters, 2014, 14, 5140-5147.	9.1	34
101	Hybrid nanocomposites based on conducting polymer and silicon nanowires for photovoltaic application. Journal of Luminescence, 2014, 156, 30-35.	3.1	11
102	Ni silicide nanowires analysis by atom probe tomography. Microelectronic Engineering, 2014, 120, 47-51.	2.4	5
103	Nanoscale Surface and Sub-Surface Chemical Analysis of SiGe Nanowires. Microscopy and Microanalysis, 2014, 20, 2052-2053.	0.4	1
104	Electrical characterisation of horizontal and vertical gate-all-around Si/SiGe nanowires field effect transistors. , 2014, , .		0
105	Photoluminescence enhancement of silicon nanocrystals placed in the near field of a silicon nanowire. Physical Review B, 2013, 88, .	3.2	18
106	A Group-Delay-Based Chipless RFID Humidity Tag Sensor Using Silicon Nanowires. IEEE Antennas and Wireless Propagation Letters, 2013, 12, 729-732.	4.0	76
107	Control of 10 nm scale cylinder orientation in self-organized sugar-based block copolymer thin films. Nanoscale, 2013, 5, 2637.	5.6	53
108	Si-SiC core-shell nanowires. Journal of Crystal Growth, 2013, 363, 158-163.	1.5	29

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109	Fabrication of silicon nanowire networks for biological sensing. Sensors and Actuators B: Chemical, 2013, 182, 390-395.	7.8	48
110	Sequential growth of bistable copper-molybdenum coordination nanolayers on inorganic surfaces. Dalton Transactions, 2013, 42, 8034.	3.3	8
111	Comparative Study on Dry Etching of $\hat{1}\pm$ - and $\hat{1}^2$ -SiC Nano-Pillars. Materials Science Forum, 2013, 740-742, 817-820.	0.3	0
112	Block copolymer technology applied to nanoelectronics. Physica Status Solidi C: Current Topics in Solid State Physics, 2013, 10, 1195-1206.	0.8	10
113	Fabrication of high-density Si and $\text{Si}_x\text{Ge}_{1-x}$ nanowire arrays based on the single step plasma etching process. Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics, 2013, 31, 041806.	1.2	11
114	High aspect ratio semiconducting nanostructure random networks: highly versatile materials for multiple applications. Physica Status Solidi - Rapid Research Letters, 2013, 7, 919-923.	2.4	16
115	Effect of HCl on the doping and shape control of silicon nanowires. Nanotechnology, 2012, 23, 215702.	2.6	64
116	Fabrication of SiC Nanopillars by Inductively Coupled SF_6/O_2 Plasma. Materials Science Forum, 2012, 711, 66-69.	0.3	2
117	Double-port AlN/Sapphire high overtone bulk acoustic resonators for the stabilization of radio-frequency oscillators. , 2012, , .		4
118	ELECTRICAL CHARACTERIZATION OF PLANAR SILICON NANOWIRE FIELD-EFFECT TRANSISTORS. International Journal of Nanoscience, 2012, 11, 1240011.	0.7	0
119	Composition and Size Effects on the Optical Properties of Isolated Silicon-Germanium Nanowires. Materials Research Society Symposia Proceedings, 2012, 1408, 3.	0.1	0
120	From planar to vertical nanowires field-effect transistors. Materials Research Society Symposia Proceedings, 2012, 1439, 101-107.	0.1	0
121	Fabrication of SiC nanopillars by inductively coupled SF_6/O_2 plasma etching. Journal Physics D: Applied Physics, 2012, 45, 235204.	2.8	35
122	PiezoNEMS: Semiconductor nanowires and heterostructures for sensing and energy harvesting. , 2012, , .		1
123	Tunable enhancement of light absorption and scattering in Si _{1-x} Ge _x nanowires. Physical Review B, 2012, 86, .		
124	Comparative study on dry etching of $\hat{1}\pm$ - and $\hat{1}^2$ -SiC nano-pillars. Materials Letters, 2012, 87, 9-12.	2.6	10
125	Ultra high density three dimensional capacitors based on Si nanowires array grown on a metal layer. Applied Physics Letters, 2012, 101, 083110.	3.3	25
126	Hidden defects in silicon nanowires. Nanotechnology, 2012, 23, 025701.	2.6	33

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127	Performance and Modeling of Si-Nanocrystal Double-Layer Memory Devices With High- κ Control Dielectrics. IEEE Transactions on Electron Devices, 2012, 59, 933-940.	3.0	11
128	Nanostructured Films Made from Zwitterionic Phosphorylcholine Diblock Copolymer Systems. Macromolecules, 2011, 44, 2240-2244.	4.8	6
129	High-performance silicon nanowire field-effect transistor with silicided contacts. Semiconductor Science and Technology, 2011, 26, 085020.	2.0	40
130	NEMS nanostructures with enhanced piezoresistive and piezoelectric properties. Application to sensor devices and energy harvesting. , 2011, , .		0
131	Carburization of Si Microwires by Chemical Vapour Deposition. Journal of Nanoscience and Nanotechnology, 2011, 11, 8412-8415.	0.9	1
132	Controlled growth of SiGe nanowires by addition of HCl in the gas phase. Journal of Applied Physics, 2011, 110, 024311.	2.5	26
133	Electrical characteristics of a vertically integrated field-effect transistor using non-intentionally doped Si nanowires. Microelectronic Engineering, 2011, 88, 3312-3315.	2.4	17
134	From Si nanowire to SiC nanotube. Journal of Nanoparticle Research, 2011, 13, 5425-5433.	1.9	23
135	Growth and characterization of gold catalyzed SiGe nanowires and alternative metal-catalyzed Si nanowires. Nanoscale Research Letters, 2011, 6, 187.	5.7	19
136	Study of CVD nanowire high-k metal interface quality for interconnect level MOS devices. Microelectronic Engineering, 2011, 88, 1228-1231.	2.4	0
137	Patterned growth of high aspect ratio silicon wire arrays at moderate temperature. Journal of Crystal Growth, 2011, 321, 151-156.	1.5	10
138	Direct top-down ordering of diblock copolymers through nanoimprint lithography. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2011, 29, 06F208.	1.2	10
139	Vertically integrated silicon-germanium nanowire field-effect transistor. Applied Physics Letters, 2011, 99, 193107.	3.3	23
140	An improved AFM cross-sectional method for piezoelectric nanostructures properties investigation: application to GaN nanowires. Nanotechnology, 2011, 22, 105704.	2.6	33
141	Strategies for Patterning Silicon Nanostructures with Diblock Copolymers, in View of Application to Microelectronics and Optoelectronics. Science of Advanced Materials, 2011, 3, 490-495.	0.7	2
142	Off axis holography of doped and intrinsic silicon nanowires: Interpretation and influence of fields in the vacuum. Journal of Physics: Conference Series, 2010, 209, 012027.	0.4	4
143	The Benefits of HCl in the Growth of Silicon Nanowires by Chemical Vapour Deposition: Growth of Small Diameter Nanowires and Controlled Facet Evolution. Materials Research Society Symposia Proceedings, 2010, 1258, 1.	0.1	0
144	Passivated TiN nanocrystals/SiN trapping layer for enhanced erasing in nonvolatile memory. Applied Physics Letters, 2010, 97, 152112.	3.3	14

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145	Silicon nanowires: Diameter dependence of growth rate and delay in growth. Applied Physics Letters, 2010, 96, .	3.3	64
146	Silicon nanowires for multisensing applications. , 2010, , .		0
147	CMOS compatible strategy based on selective atomic layer deposition of a hard mask for transferring block copolymer lithography patterns. Nanotechnology, 2010, 21, 435301.	2.6	28
148	The Importance of the Radial Growth in the Faceting of Silicon Nanowires. Nano Letters, 2010, 10, 2335-2341.	9.1	49
149	Hybrid silicon nanocrystals/SiN charge trapping layer with high-k dielectrics for FN and CHE programming. , 2010, , .		5
150	The effects of HCl on silicon nanowire growth: surface chlorination and existence of a \hat{a} -diffusion-limited minimum diameter \hat{a} ™. Nanotechnology, 2009, 20, 475307.	2.6	41
151	Self-assembling study of a cylinder-forming block copolymer via a nucleation \hat{a} “growth mechanism. Nanotechnology, 2009, 20, 095602.	2.6	11
152	The morphology of silicon nanowires grown in the presence of trimethylaluminium. Nanotechnology, 2009, 20, 245602.	2.6	16
153	Growth and low temperature photoluminescence of silicon nanowires for different catalysts. Materials Research Society Symposia Proceedings, 2009, 1178, 50.	0.1	0
154	Self-connected horizontal silicon nanowire field effect transistor. Solid State Communications, 2009, 149, 799-801.	1.9	10
155	Chemical-vapour-deposition growth and electrical characterization of intrinsic silicon nanowires. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2009, 159-160, 83-86.	3.5	6
156	Photoluminescence of silicon nanowires obtained by epitaxial chemical vapor deposition. Physica E: Low-Dimensional Systems and Nanostructures, 2009, 41, 963-965.	2.7	14
157	High \hat{a} “density guided growth of silicon nanowires in nanoporous alumina on Si(100) substrate: Estimation of activation energy. Physica Status Solidi - Rapid Research Letters, 2009, 3, 19-21.	2.4	10
158	Size Effects in Mechanical Deformation and Fracture of Cantilevered Silicon Nanowires. Nano Letters, 2009, 9, 525-529.	9.1	216
159	Performance and Reliability of Si-Nanocrystal Double Layer Memory Devices with High-k Control Dielectrics. , 2009, , .		0
160	Silicon nanowires grown in nanoporous alumina matrices on oriented silicon substrates investigated by electron microscopy. Superlattices and Microstructures, 2008, 44, 354-361.	3.1	6
161	A new architecture for self \hat{a} “organized silicon nanowire growth integrated on a \hat{a} “100 \hat{a} “% silicon substrate. Physica Status Solidi (A) Applications and Materials Science, 2008, 205, 1606-1614.	1.8	10
162	The growth of small diameter silicon nanowires to nanotrees. Nanotechnology, 2008, 19, 125608.	2.6	42

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163	Control of Gold Surface Diffusion on Si Nanowires. Nano Letters, 2008, 8, 1544-1550.	9.1	108
164	Fabrication of Well-Organized and Densely Packed Si Nanopillars Containing SiGe Nanodots by Using Block Copolymer Templates. Chemistry of Materials, 2008, 20, 6183-6188.	6.7	13
165	Direct Quantification of Gold along a Single Si Nanowire. Nano Letters, 2008, 8, 3709-3714.	9.1	46
166	Photoluminescence of confined electron-hole plasma in core-shell silicon/silicon oxide nanowires. Applied Physics Letters, 2008, 93, .	3.3	20
167	Optical manipulation of silicon nanowires on silicon nitride waveguides. , 2008, , .		1
168	Surface chemistry along a single silicon nanowire: Quantitative x-ray photoelectron emission microscopy (XPEEM) of the metal catalyst diffusion. , 2008, , 151-152.		0
169	Critical condition for growth of silicon nanowires. Journal of Applied Physics, 2007, 102, 094906.	2.5	55
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